

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE30P25S uses advanced trench technology to provide excellent $R_{\text{DS}(\text{ON})}$, This device is suitable for use as a load switch or power management.

General Features

• $V_{DS} = -30V, I_{D} = -25A$

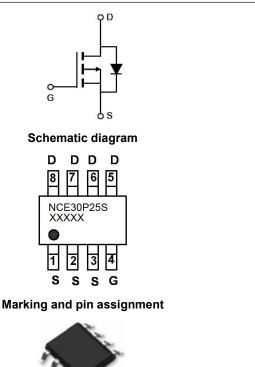
 $R_{DS(ON)}$ <9m Ω @ V_{GS} =-10V

 $R_{DS(ON)}$ <14m Ω @ V_{GS} =-4.5V

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- Power management
- Load switch





SOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE30P25S	NCE30P25S	SOP-8	Ø330mm	12mm	4000 units

Absolute Maximum Ratings (T₄=25 °C unless otherwise noted)

7 to colore maximum reasings (1 A 20 colored to the total)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	Vos	-30	V			
Gate-Source Voltage	Vgs	±20	V			
Drain Current-Continuous	I _D	-25	А			
Drain Current-Pulsed (Note 1)	I _{DM}	-100	А			
Maximum Power Dissipation	Po	3.5	W			
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	°C			

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	36	°C/W
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250µA	-30		-	V



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NCE30P25S

Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V,V _{GS} =0V	-	-	-1	μΑ
Gate-Body Leakage Current	Igss	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	·					
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-1.0	-1.5	-2.5	V
	R _{DS(ON)}	V _{GS} =-10V, I _D =-15A	-	6.4	9	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-15A	-	8.3	14	
Forward Transconductance	g FS	V _{DS} =-10V,I _D =-15A	30	-	-	S
Dynamic Characteristics (Note4)	·					
Input Capacitance	C _{lss}	\/ - 45\/\/ -0\/		7506	8500	PF
Output Capacitance	Coss	V_{DS} =-15V, V_{GS} =0V, F=1.0MHz	-	901	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UMH2	-	742	-	PF
Switching Characteristics (Note 4)			•			
Turn-on Delay Time	t _{d(on)}		-	50	-	nS
Turn-on Rise Time	t _r	V _{DD} =-15V, I _D =-15A,	-	60	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10V, R_{GEN} =3 Ω	-	60	-	nS
Turn-Off Fall Time	t _f		-	21	-	nS
Total Gate Charge	Qg		-	98.9	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =-15V,I _D =-15A,V _{GS} =-10V	-	11.4	-	nC
Gate-Drain Charge	Q _{gd}		-	20.3	-	nC
Drain-Source Diode Characteristics			•	•		
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-25A	-	-	-1.2	V
	<u> </u>	•				

Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

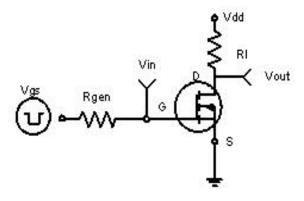


Figure 1 Switching Test Circuit

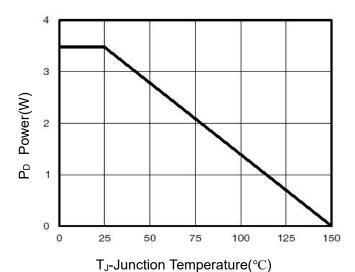


Figure 3 Power Dissipation

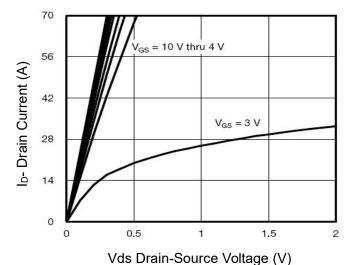


Figure 5 Output Characteristics

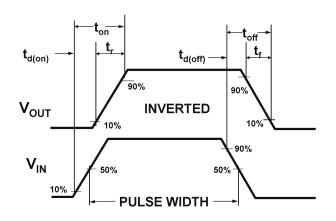
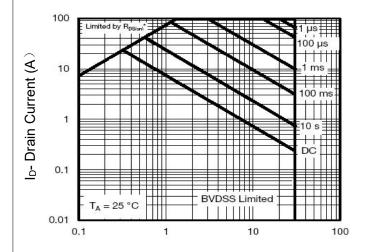


Figure 2 Switching Waveforms



Vds Drain-Source Voltage (V)
Figure 4 Safe Operation Area

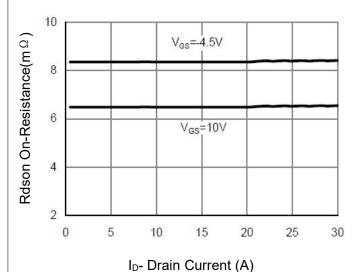
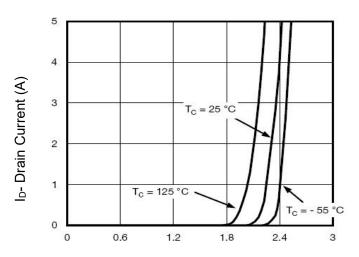


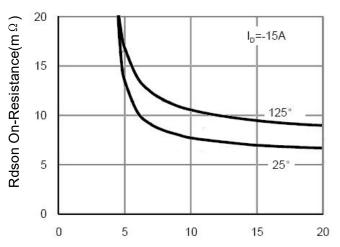
Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)





Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

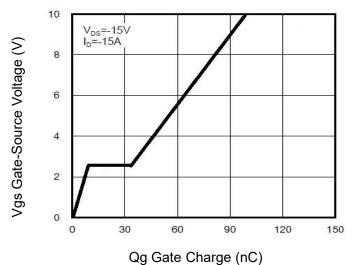
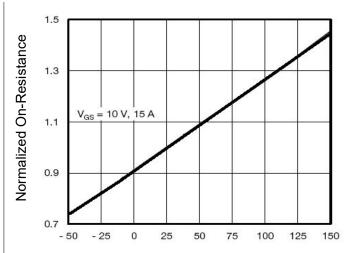


Figure 11 Gate Charge



T_J-Junction Temperature(°C)

Figure 8 Drain-Source On-Resistance

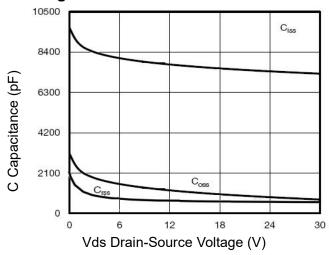


Figure 10 Capacitance vs Vds

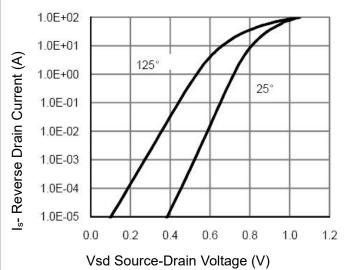


Figure 12 Source- Drain Diode Forward



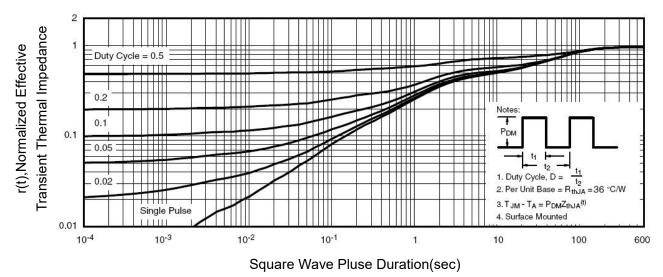
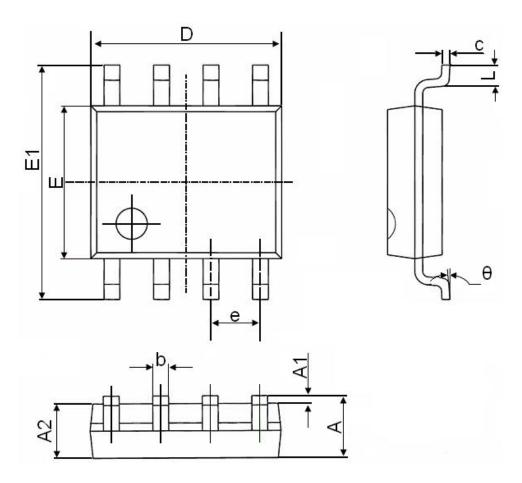


Figure 13 Normalized Maximum Transient Thermal Impedance



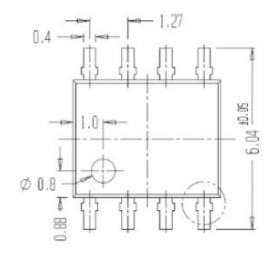
SOP-8 (C) Package Information

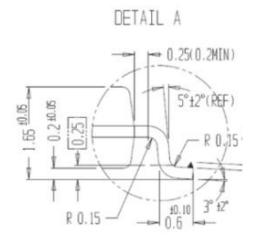


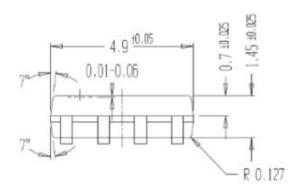
Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270(BSC)		0.050	(BSC)	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	

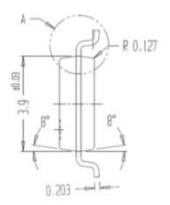


SOP-8 (R) Package InformationSOP-8 Package Information









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